



## Photodetector Materials and Optoelectronic Devices

Guest Editors:

**Dr. Ziqing Li**

Institute of Optoelectronics,  
Fudan University, Shanghai  
200433, China

**Dr. Weixin Ouyang**

School of Physical Science and  
Technology, Northwestern  
Polytechnical University, Xi'an,  
China

Deadline for manuscript  
submissions:

**closed (10 April 2024)**

### Message from the Guest Editors

Optoelectronic devices are special types of semiconductor devices that are able to convert light energy into electrical energy, or electrical energy into light energy. This Special Issue aims to collect research articles concerning this topic to show the advantages of low-dimensional nanostructures in photodetector and optoelectronic devices. Topics include, but are not limited to, the following:

- Ultraviolet photodetecting technology and its application;
- Visible-light photodetecting technology and its application;
- Infrared photodetecting technology and its application;
- Terahertz photodetecting technology and its application;
- Weak-light photodetecting technology and its application;
- Polarization photodetecting technology and its application;
- Broadband and narrowband photodetecting technology and its application;
- High-speed imaging applications;
- High-sensitivity X-ray detector;
- High-performance LED technology;
- High-efficiency solar cell applications;
- Design and optimization of optoelectronic materials, etc.

